

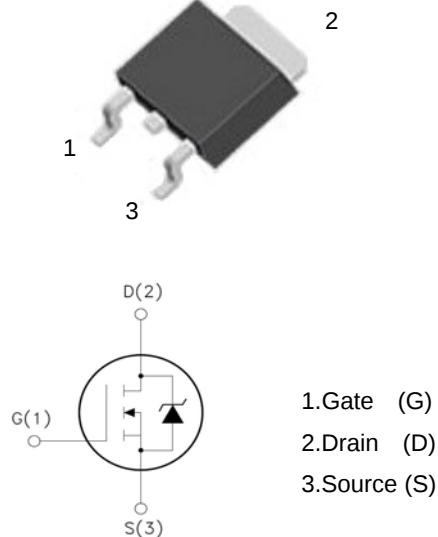
CTKD60N04

40V N-Channel MOSFET

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 29nC (Typ.).
- ☐ BVDSS=40V, I_D=60A
- ☐ R_{DS(on)} : 0.008Ω (Max) @V_G=10V
- ☐ 100% Avalanche Tested

TO-252



Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain-Source Voltage		40	V
I _D	Drain Current	T _C =25°C	60	A
		T _C =100°C	42	
V _{GS(TH)}	Gate Threshold Voltage		±25	V
E _{AS}	Single Pulse Avalanche Energy (note5)		400	mJ
I _{AR}	Avalanche Current (note2)		60	A
P _D	Power Dissipation (Ta=25°C)		65	W
T _j	Junction Temperature(Max)		175	°C
T _{stg}	Storage Temperature		-55~+175	
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	2.3	°C/W

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	7.3	8	m Ω
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =20A	15	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	1800	-	PF
Output Capacitance	C _{OSS}		-	280	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	190	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, I _D =2A, R _L =1Ω V _{GS} =10V, R _G =3Ω	-	6.4	-	nS
Turn-on Rise Time	t _r		-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	29		nC
Gate-Source Charge	Q _{gs}		-	4.5		nC
Gate-Drain Charge	Q _{gd}		-	6.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs ^(Note3)	-	29	-	nS
Reverse Recovery Charge	Q _{rr}		-	26	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega$.

Typical Characteristics

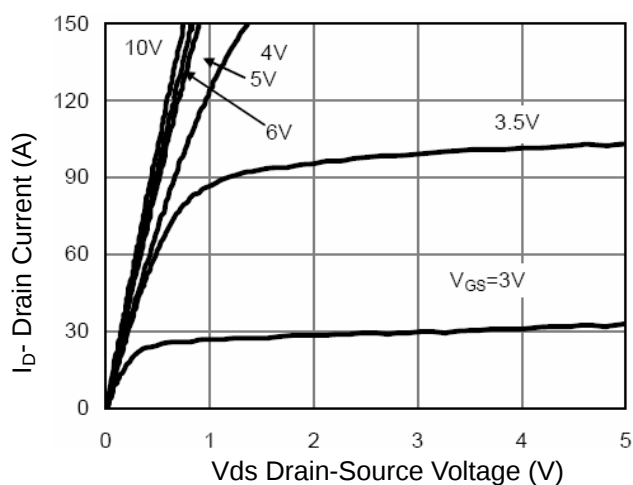


Figure 1 Output Characteristics

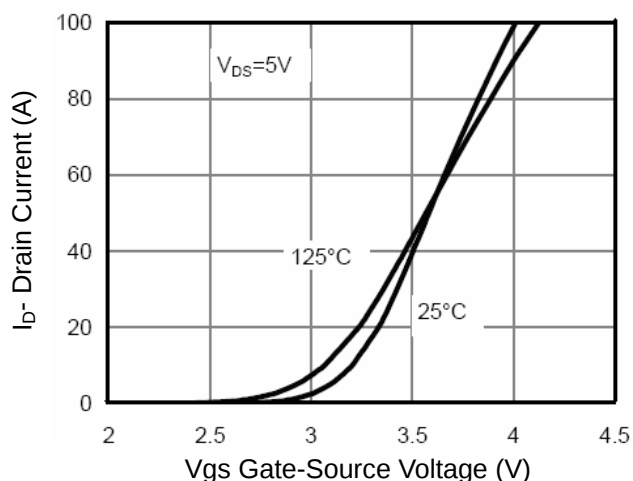


Figure 2 Transfer Characteristics

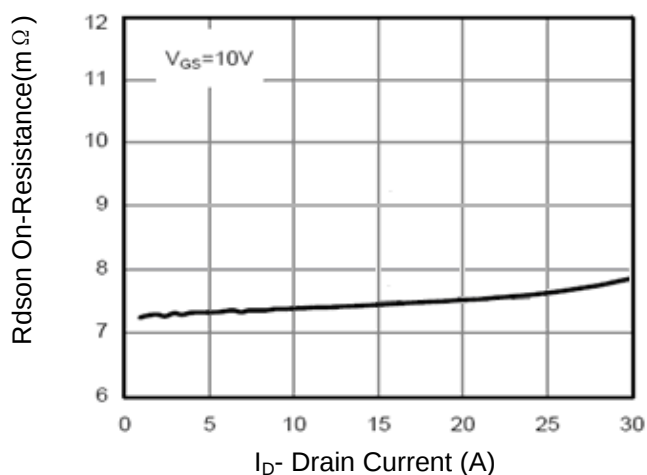


Figure 3 Rdson- Drain Current

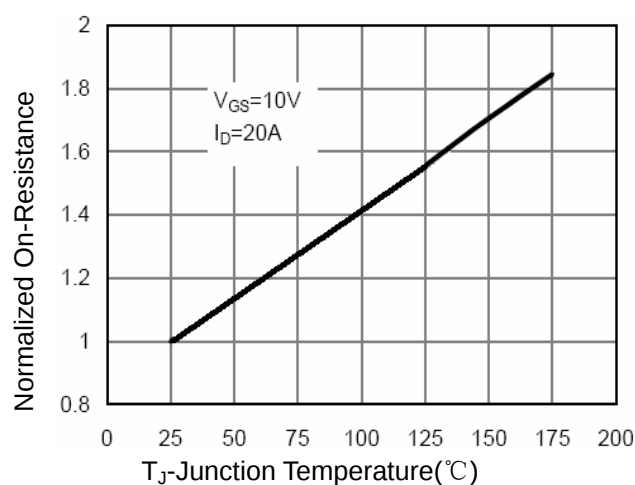


Figure 4 Rdson-Junction Temperature

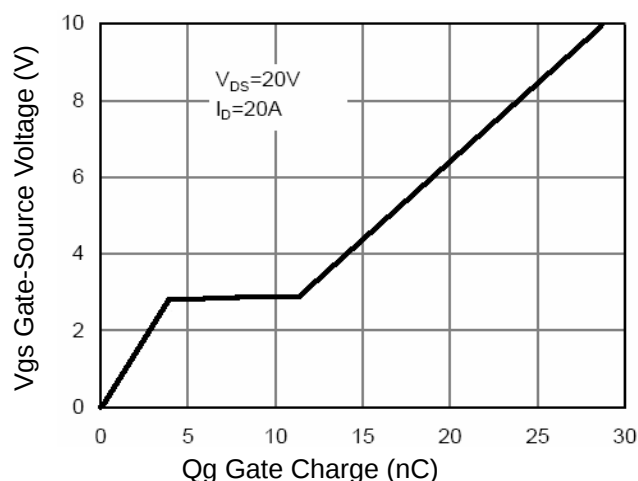


Figure 5 Gate Charge

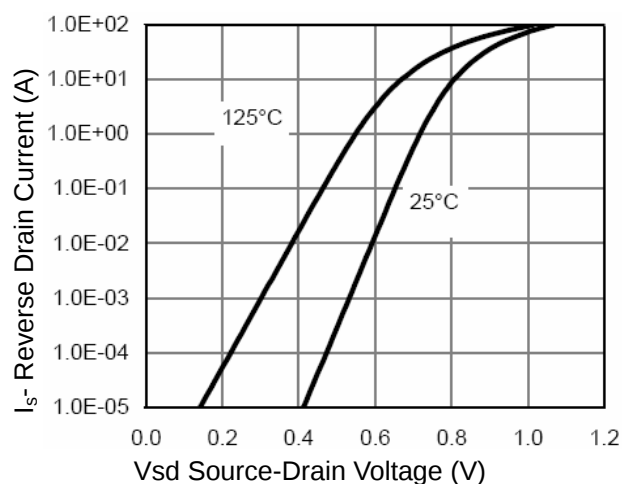


Figure 6 Source- Drain Diode Forward

Typical Characteristics (Continued)

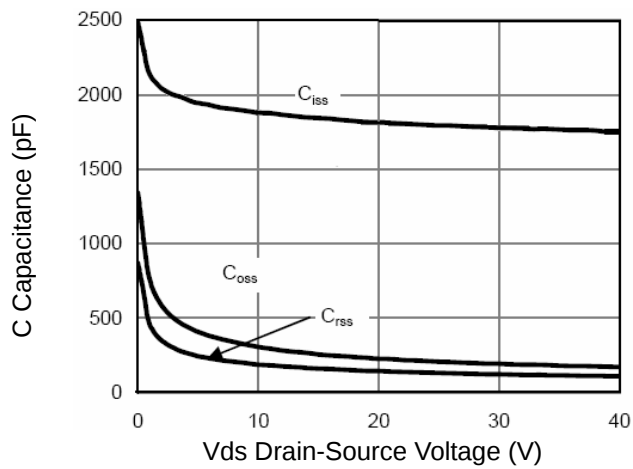


Figure 7 Capacitance vs Vds

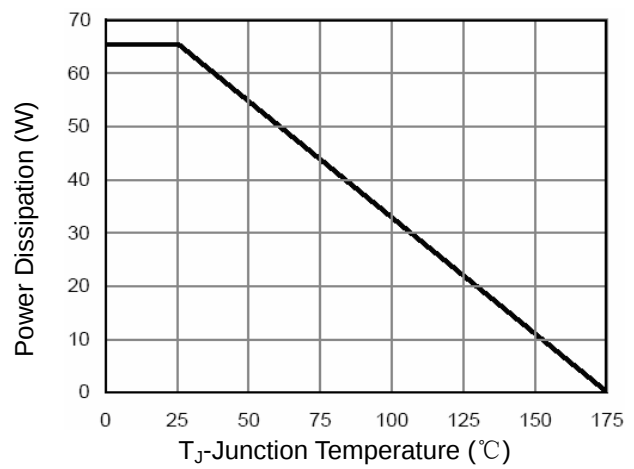


Figure 9 Power De-rating

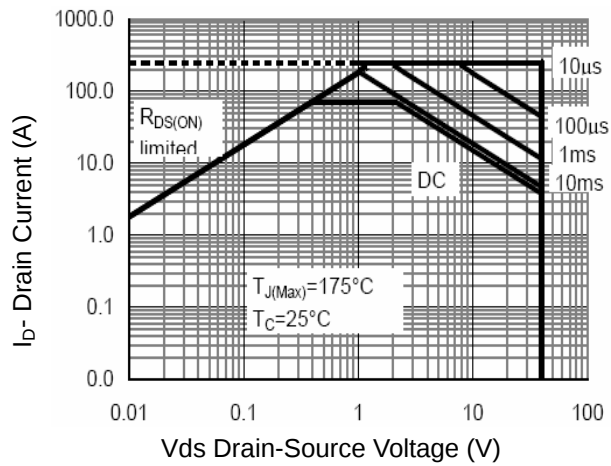


Figure 8 Safe Operation Area

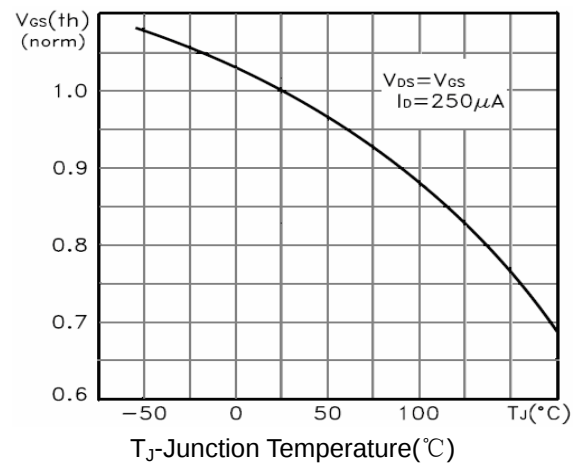


Figure 10 $V_{GS(th)}$ vs Junction Temperature

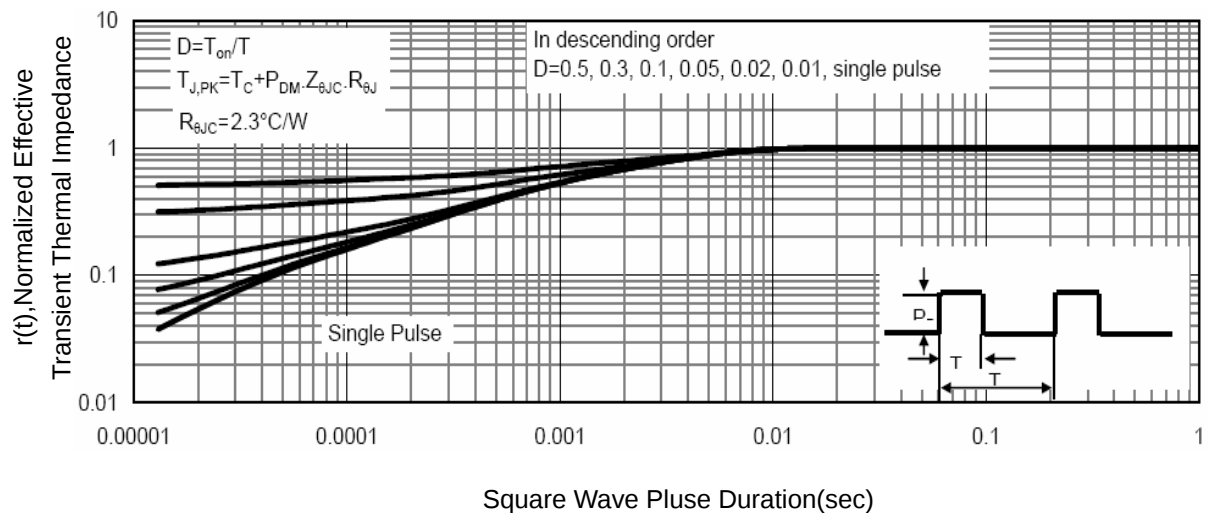
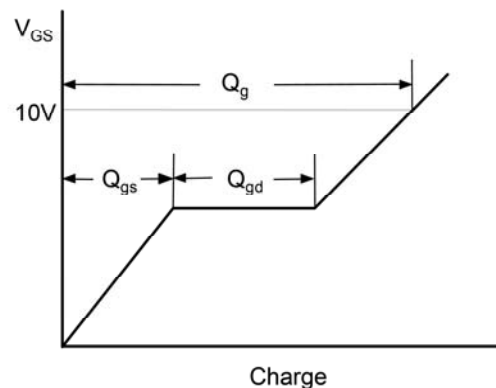
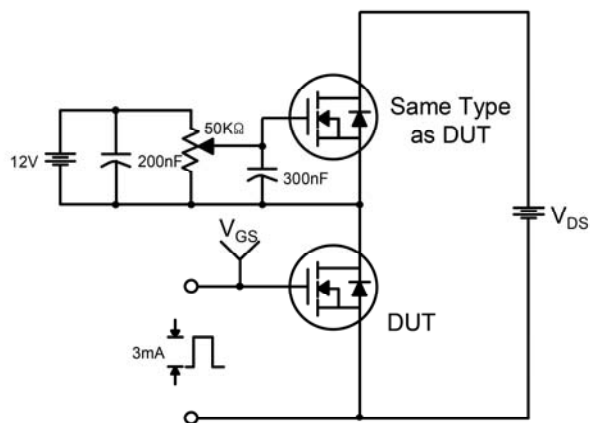
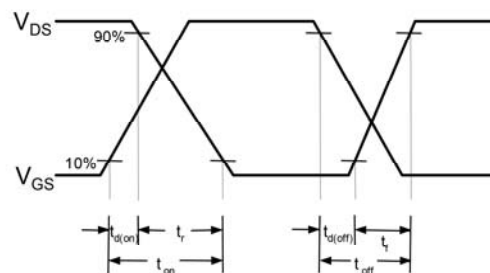
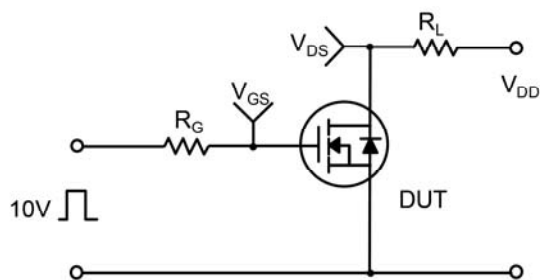


Figure 11 Normalized Maximum Transient Thermal Impedance

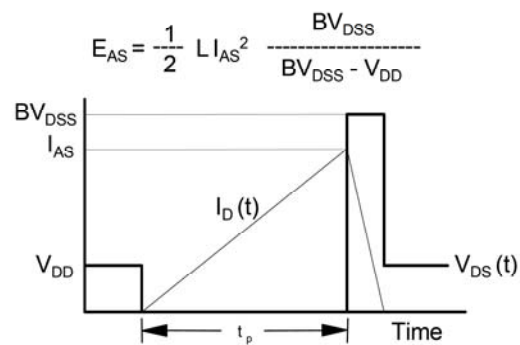
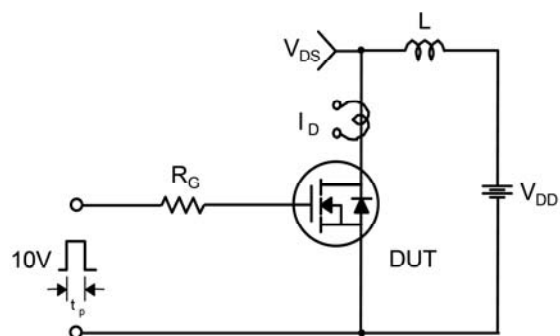
Gate Charge Test Circuit & Waveform

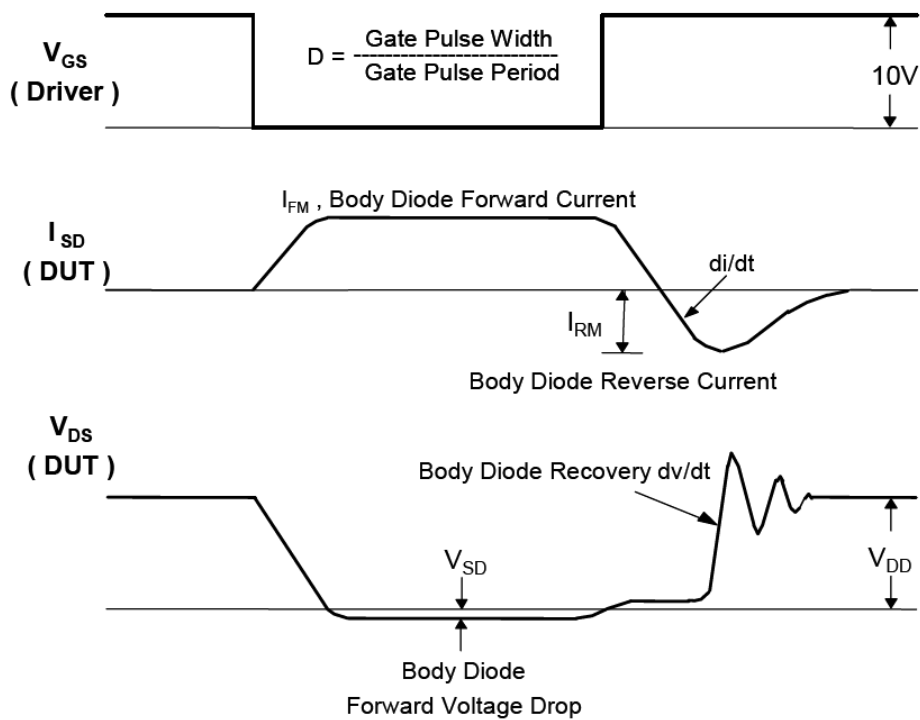
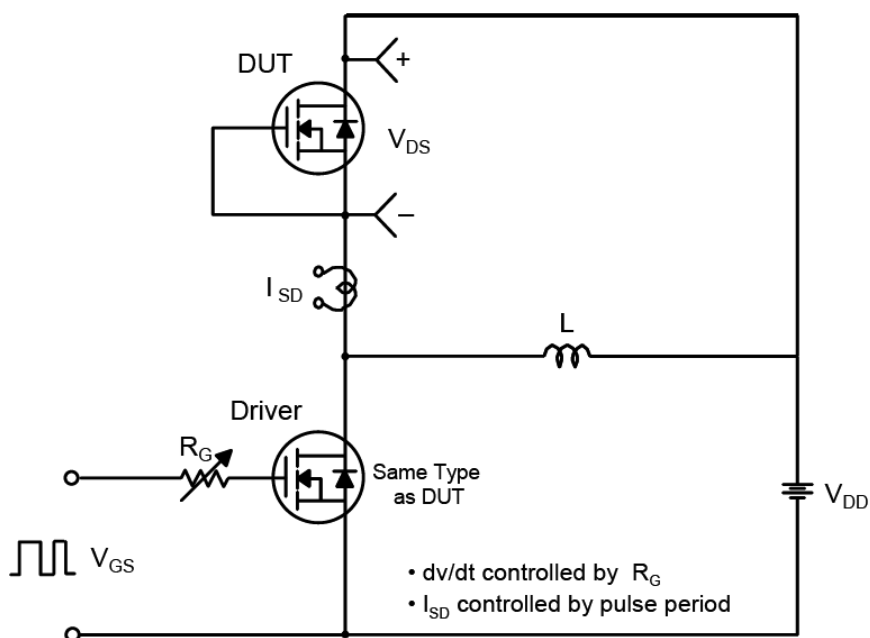


Resistive Switching Test Circuit & Waveforms



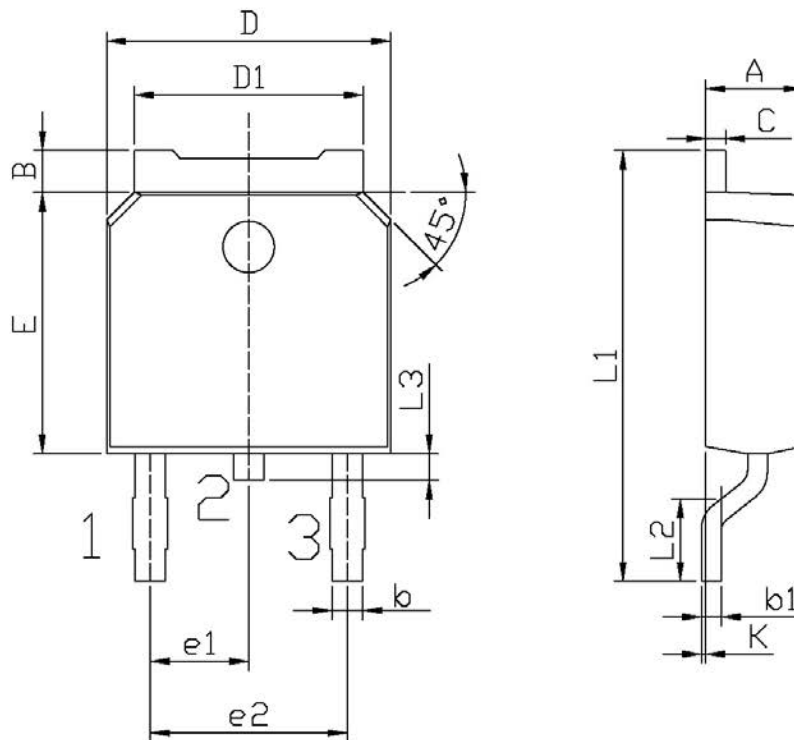
Unclamped Inductive Switching Test Circuit & Waveforms





Package Dimension

TO-252 Unit: mm



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.20	5.40	K	0.00	0.10